



>=9>=9'A=7FC9@97HFCB=7G'7C"ž'@H8"

>L\$%% I '%5'GYbg]h]jY'G7F'

FYj'5"&"%

^ Z / W d / K E W

The JX011U SCR provides high dV/dt rate
with strong resistance to electromagnetic



Peak gate power	P_{GM}	2	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	1	kV

BCH9%. Operating junction temperature T_j is up to 125 when a resistor 1k is connected between Gate and Cathode. Without this resistor, the T_j is up to 110 only.

> d Z / > , Z d Z / $T_j=25$ / unless otherwise specified)

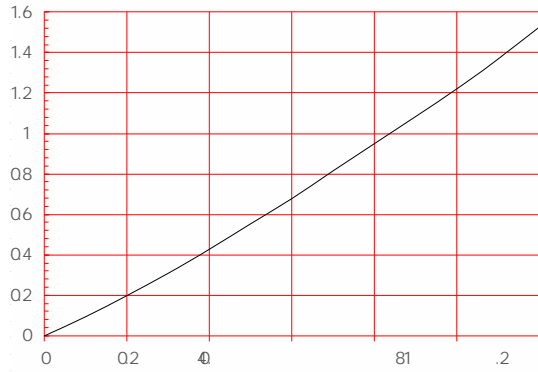
Gma Vc''	HYgh' 7 cbX]h]cb'	JU' iY'			I b]h'
		A=B''	HMD''	A5L''	
I_{GT}	$V_D=12V R_L=33$	-	40	200	μA
V_{GT}		-	0.6	0.8	V
V_{GD}	$V_D=V_{DRM} T_j=125$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	5	mA
I_H	$I_T=0.05A$	-	-	4	mA
dV/dt	$V_D=540V T_j=125 R_{GK}=1k$	200	-	-	V/ μs
	$V_D=540V T_j=125 R_{GK}=220$	500	-	-	
t_{on}	$I_G=10mA I_A=20mA I_R=2mA$	-	2	-	μs
t_{off}	$T_j=25$	-	50	-	μs

^d d / , Z d Z / ^d / ^

Gma Vc''	DUfU a YhYf'	JU' iYf]A5L'L'	I b]h'
V_{TM}	$I_T=2A t_p=380\mu s$ $T_j=25$	1.4	

:= ; "% . Maximum power dissipation versus RMS on-state current

:= ; "& . RMS on-state current versus case temperature



>L\$%% I'

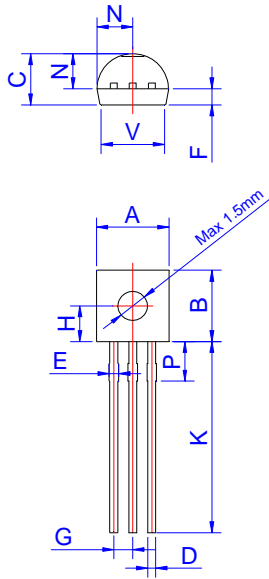
KZ Z/E' /E&KZD d/KE

CfXYf'WcXY'	Jc`hU[Y' J8FA#JFFA'flJL'	= ; Hfl 5L'	DUW_U[Y'	6UgY'ehm" fidWgL'	8Y]jYfm' a cXY'
>L\$%% I'	,\$\$'	@&\$\$'	HC!-&'	%z\$\$\$'	6 i`_'DUW_'
>L\$%% I!HF'				&z\$\$\$'	HUdY' /'FYY'

8cWi a Ybh'FY j]g]cb' <]ghcfm'

Date	Revision	Changes
Apr.12, 2023	A.1.0	Last update
Mar.28, 2025	A.2.0	Renew PACKAGE MECHANICAL DATA
Sept.28, 2025	A.2.1	Revise PACKAGE MECHANICAL DATA

W < ' D , E / > d




Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.50		0.70			
F	1.10					
G				0.043		
H	2.20			0.087		
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
N	2.04		2.66	0.080		0.105
P	1.80	10	2.30	0.071		0.091
V	4.10		4.50	0.161		0.177

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